RCX120N20

Nch 200V 12A Power MOSFE Datasheet

V_{DSS}	200V
$R_{DS(on)}$ (Max.)	325mΩ
I_D	12A
P_D	40W

●Outline

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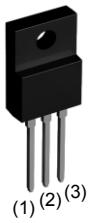


●Features

1) Low on-resistance.

2) Fast switching speed.

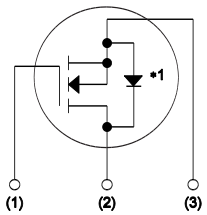
3) Drive circuits can be simple.

4) Parallel use is easy.

5) Pb-free lead plating ; RoHS compliant

6) 100% Avalanche tested

●Inner circuit



(1) Gate
(2) Drain
(3) Source

∗1 BODY DIODE

●Application

Switching Power Supply

Automotive Motor Drive

Automotive Solenoid Drive

●Packaging specifications

Type	Packaging	Bulk
	Reel size (mm)	-
	Tape width (mm)	-
	Basic ordering unit (pcs)	500
	Taping code	-
	Marking	RCX120N20

●Absolute maximum ratings (T_a = 25°C)

Parameter		Symbol	Value	Unit
Drain - Source voltage		V_{DSS}	200	V
Continuous drain current	T_c = 25°C	I_D *1	±12	A
	T_c = 100°C	I_D *1	±6.5	A
Pulsed drain current		$I_{D,pulse}$ *2	±48	A
Gate - Source voltage		V_{GSS}	±30	V
Avalanche energy, single pulse		E_{AS} *3	11.6	mJ
Avalanche current		I_{AR} *3	6.0	A
Power dissipation	T_c = 25°C	P_D	40	W
	T_a = 25°C	P_D	2.23	W
Junction temperature		T_j	150	°C
Range of storage temperature		T_{stg}	−55 to +150	°C

●Thermal resistance

Parameter	Symbol	Values			Unit
		Min.	Typ.	Max.	
Thermal resistance, junction - case	R_{thJC}	-	-	3.125	°C/W
Thermal resistance, junction - ambient	R_{thJA}	-	-	56	°C/W
Soldering temperature, wavesoldering for 10s	T_{sold}	-	-	265	°C

●Electrical characteristics (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Drain - Source breakdown voltage	$V_{(BR)DSS}$	V_{GS} = 0V, I_D = 1mA	200	-	-	V
Zero gate voltage drain current	I_{DSS}	V_{DS} = 200V, V_{GS} = 0V T_j = 25°C	-	-	10	μA
		V_{DS} = 200V, V_{GS} = 0V T_j = 125°C	-	-	100	
Gate - Source leakage current	I_{GSS}	V_{GS} = ±30V, V_{DS} = 0V	-	-	±100	nA
Gate threshold voltage	$V_{GS\ (th)}$	V_{DS} = 10V, I_D = 1mA	3.25	-	5.25	V
Static drain - source on - state resistance	$R_{DS(on)}$ *4	V_{GS} = 10V, I_D = 6.0A	-	250	325	mΩ
		V_{GS} = 10V, I_D = 6.0A T_j = 125°C	-	565	790	
Forward transfer admittance	g_{fs}	V_{DS} = 10V, I_D = 6.0A	2.75	5.50	-	S

●**Electrical characteristics** (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Input capacitance	C_{iss}	V_{GS} = 0V	-	740	-	pF
Output capacitance	C_{oss}	V_{DS} = 25V	-	57	-	
Reverse transfer capacitance	C_{rss}	f = 1MHz	-	26	-	
Turn - on delay time	$t_{d(on)}$ *4	V_{DD} ≃ 100V, V_{GS} = 10V	-	20	-	ns
Rise time	t_r *4	I_D = 6.0A	-	33	-	
Turn - off delay time	$t_{d(off)}$ *4	R_L = 16.67Ω	-	27	-	
Fall time	t_f *4	R_G = 10Ω	-	11	-	

●**Gate Charge characteristics** (T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Total gate charge	Q_g *4	V_{DD} ≃ 100V	-	15	-	nC
Gate - Source charge	Q_{gs} *4	I_D = 12A	-	6	-	
Gate - Drain charge	Q_{gd} *4	V_{GS} = 10V	-	6	-	
Gate plateau voltage	$V_{(plateau)}$	V_{DD} ≃ 100V, I_D = 12A	-	7.4	-	V

●**Body diode electrical characteristics** (Source-Drain)(T_a = 25°C)

Parameter	Symbol	Conditions	Values			Unit
			Min.	Typ.	Max.	
Continuous source current	I_S *1	T_c = 25°C	-	-	12	A
Pulsed source current	I_{SM} *2		-	-	48	A
Forward voltage	V_{SD} *4	V_{GS} = 0V, I_S = 12A	-	-	1.5	V
Reverse recovery time	t_{rr} *4	I_S = 6.0A di/dt = 100A/μs	-	80	-	ns
Reverse recovery charge	Q_{rr} *4		-	290	-	nC

*1 Limited only by maximum temperature allowed.

*2 Pw ≤ 10μs, Duty cycle ≤ 1%

*3 L ≃ 500μH, V_{DD} = 50V, Rg = 25Ω, starting T_j = 25°C

*4 Pulsed

●Electrical characteristic curves

Fig.1 Power Dissipation Derating Curve

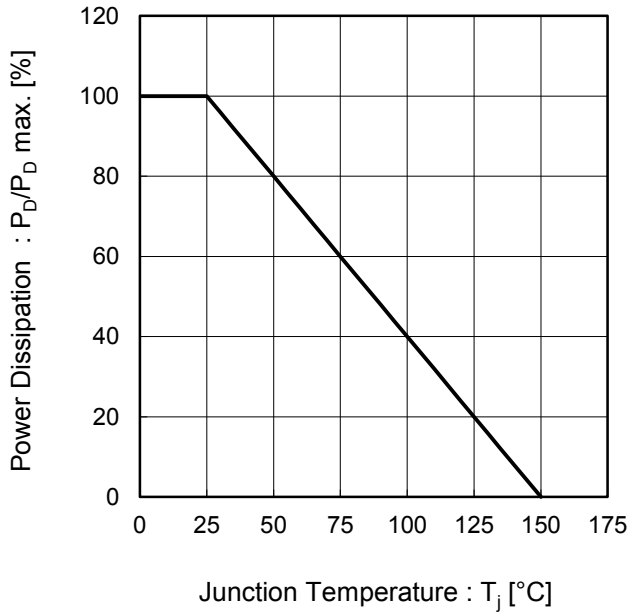


Fig.2 Maximum Safe Operating Area

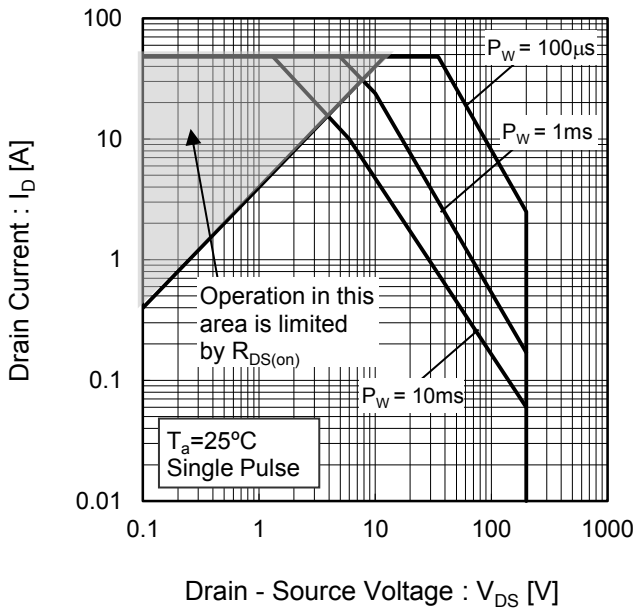
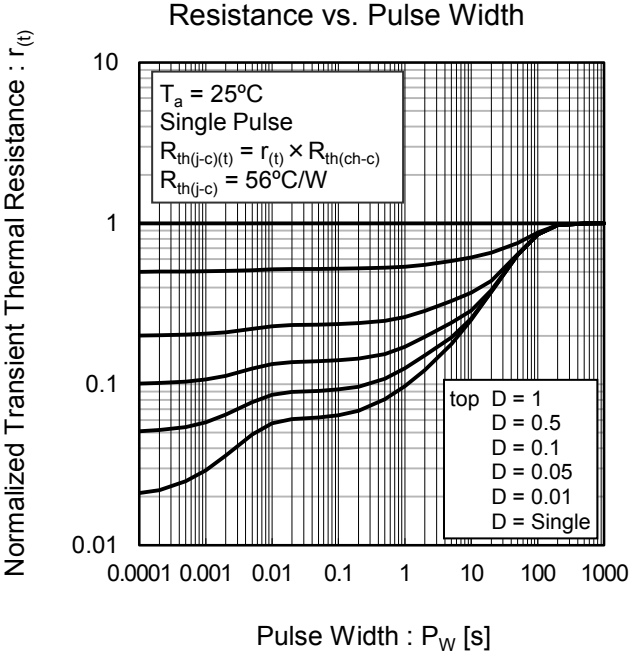


Fig.3 Normalized Transient Thermal Resistance vs. Pulse Width



●Electrical characteristic curves

Fig.4 Avalanche Current vs Inductive Load

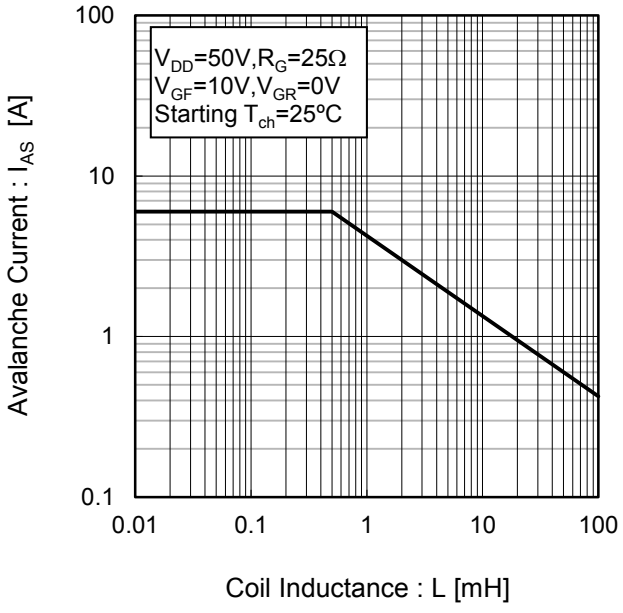


Fig.5 Avalanche Energy Derating Curve vs Junction Temperature

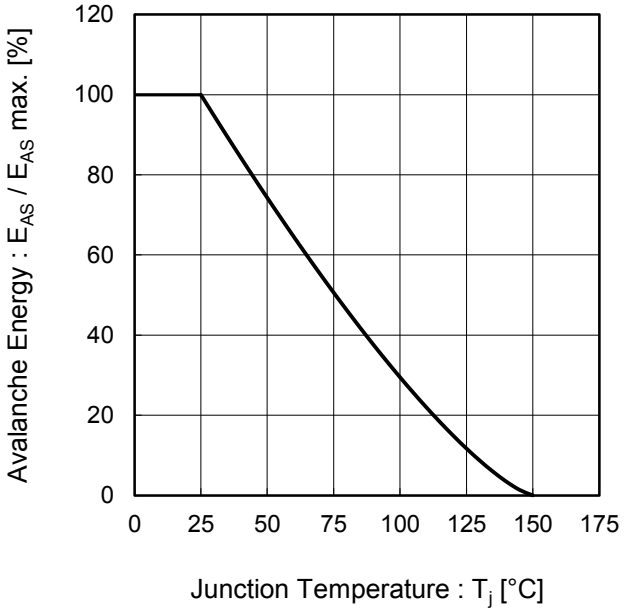


Fig.6 Typical Output Characteristics(I)

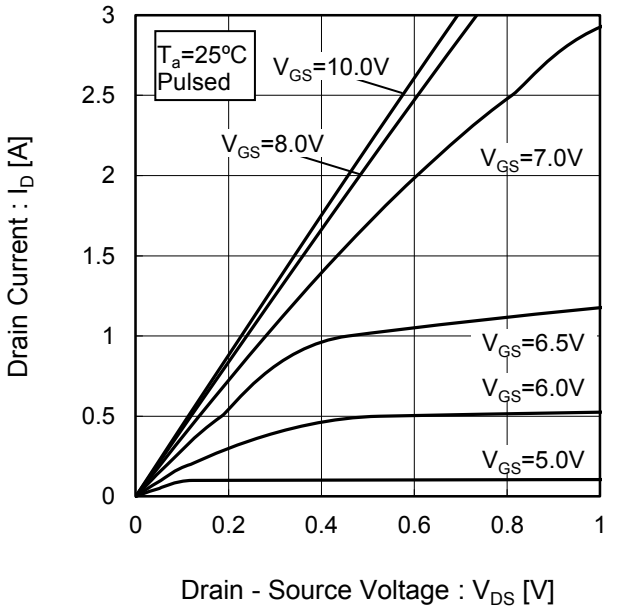
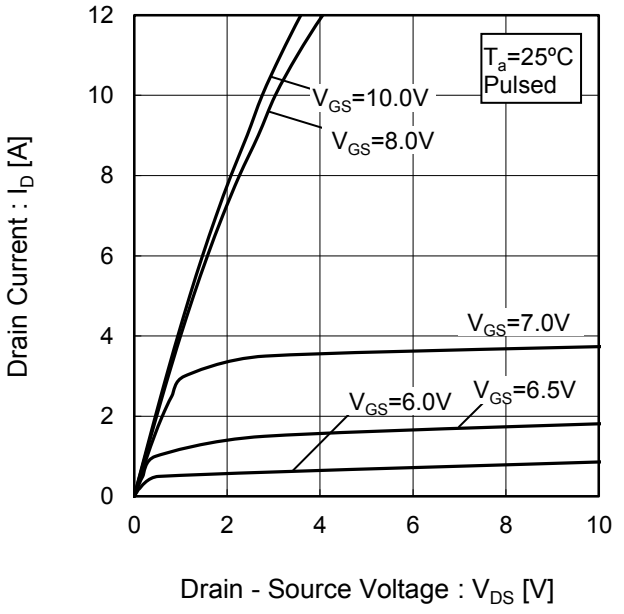


Fig.7 Typical Output Characteristics(II)



●Electrical characteristic curves

Fig.8 Breakdown Voltage vs. Junction Temperature

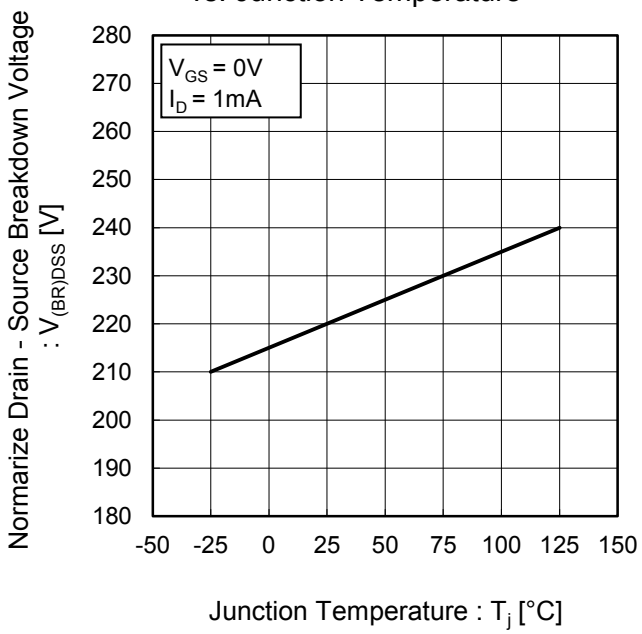


Fig.9 Typical Transfer Characteristics

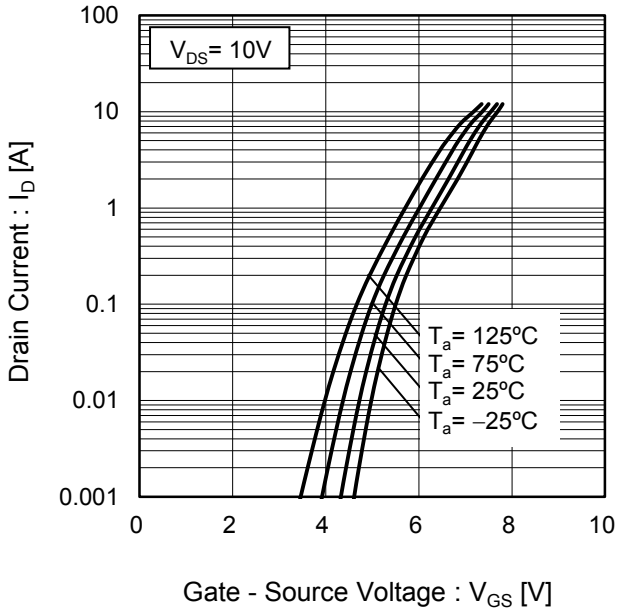


Fig.10 Gate Threshold Voltage vs. Junction Temperature

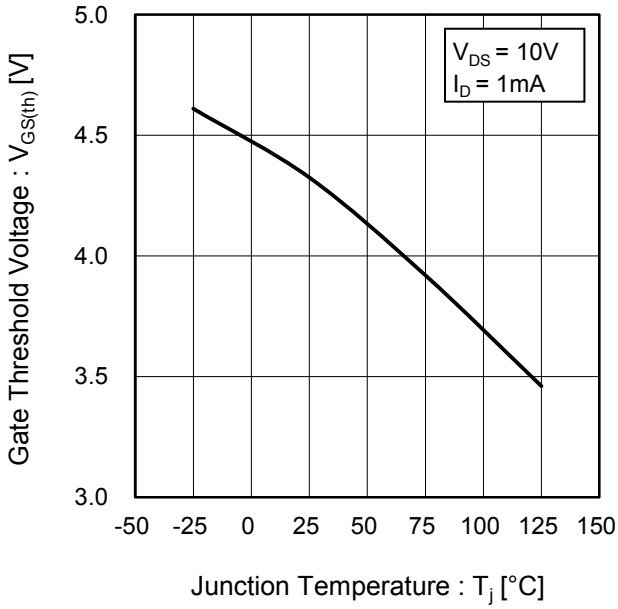
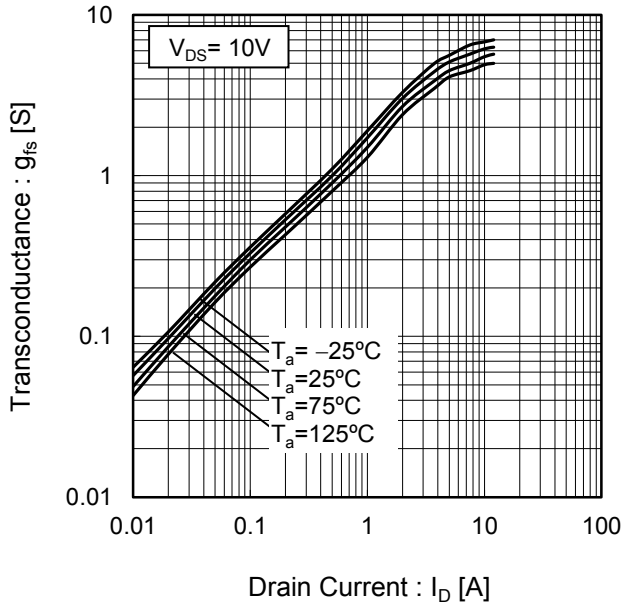


Fig.11 Transconductance vs. Drain Current



●Electrical characteristic curves

Fig.12 Static Drain - Source On - State Resistance vs. Gate Source Voltage

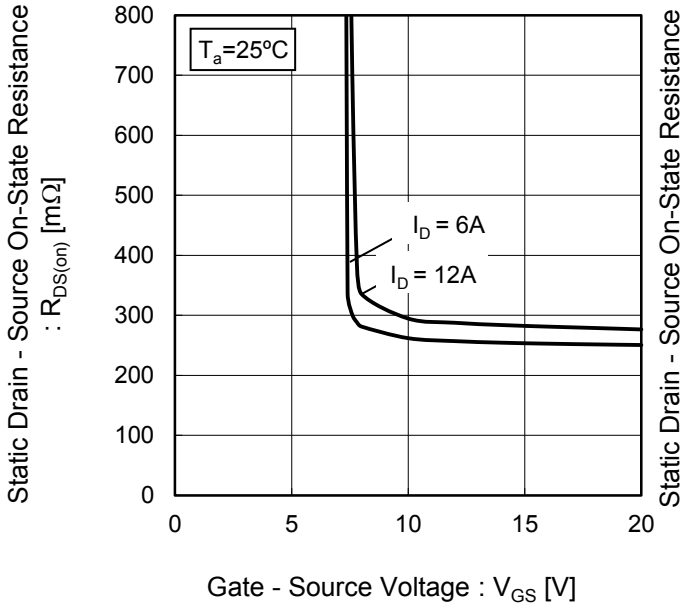


Fig.13 Static Drain - Source On - State Resistance vs. Drain Current(I)

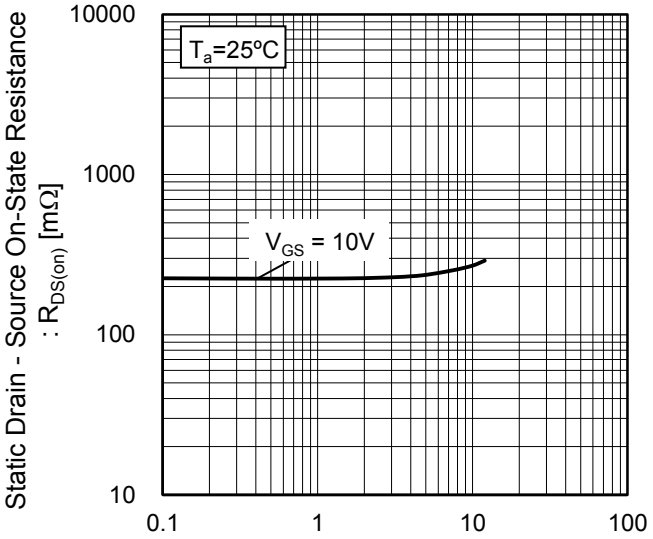
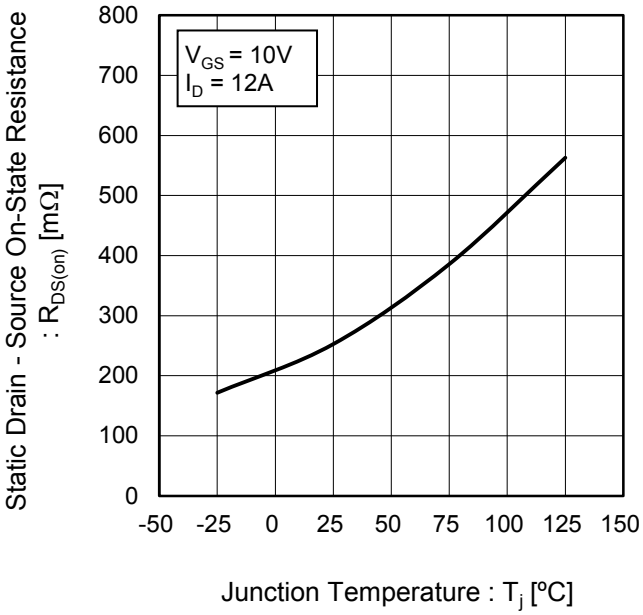


Fig.14 Static Drain - Source On - State Resistance vs. Junction Temperature



●Electrical characteristic curves

Fig.15 Static Drain - Source On - State Resistance vs. Drain Current(I)

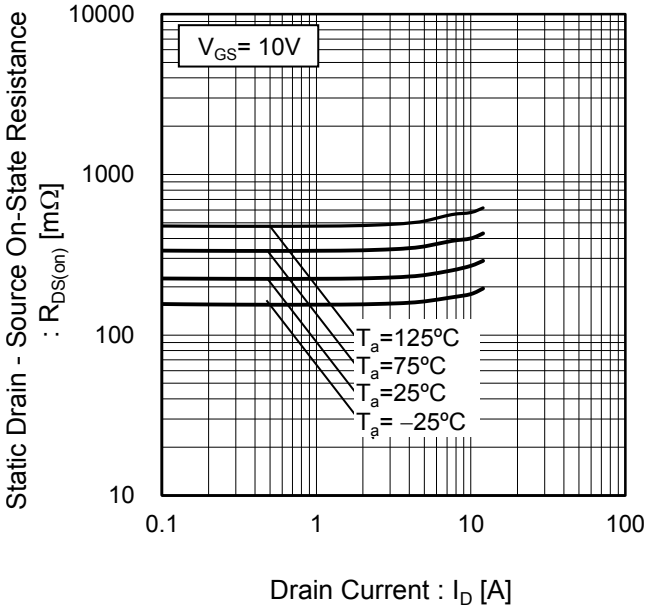
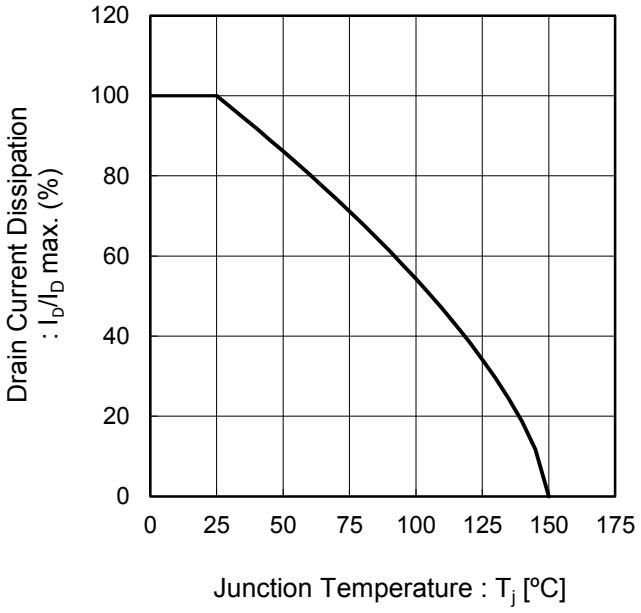


Fig.16 Drain Current Derating Curve



●Electrical characteristic curves

Fig.17 Typical Capacitance vs. Drain - Source Voltage

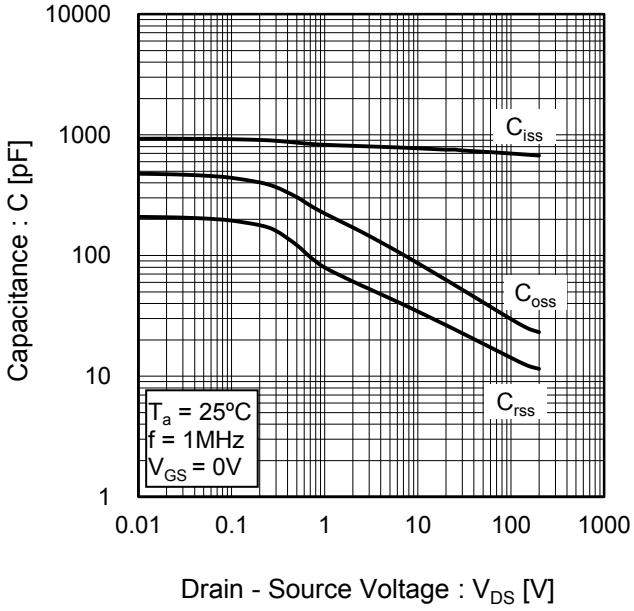


Fig.18 Switching Characteristics

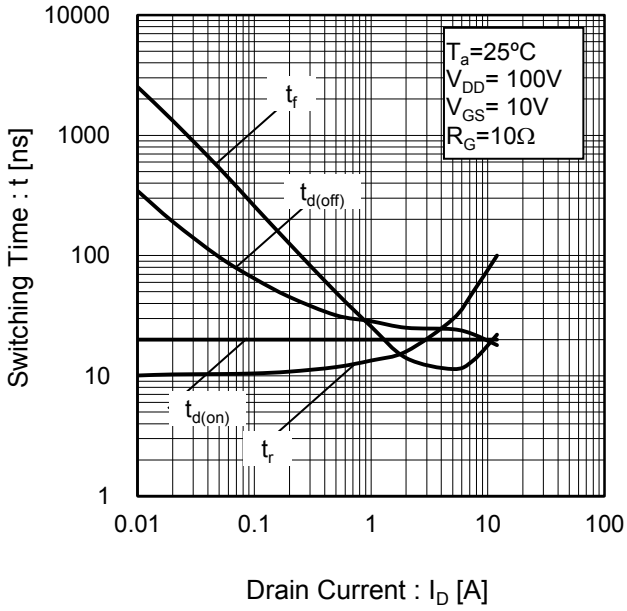
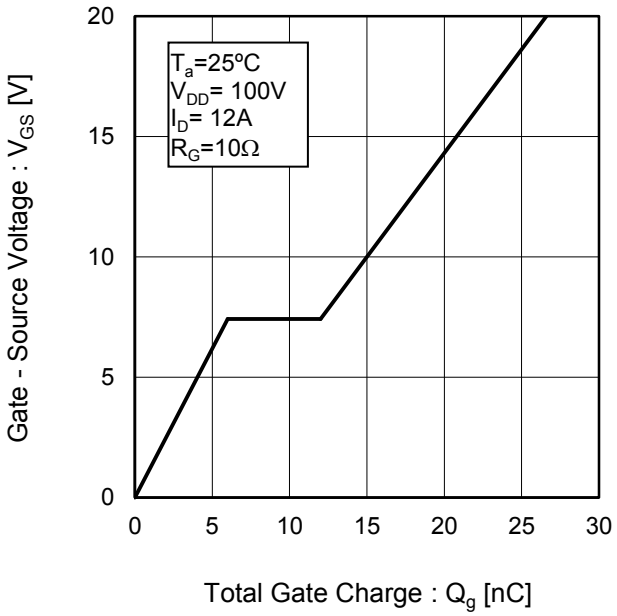


Fig.19 Dynamic Input Characteristics



●Electrical characteristic curves

Fig.20 Source Current vs. Source - Drain Voltage

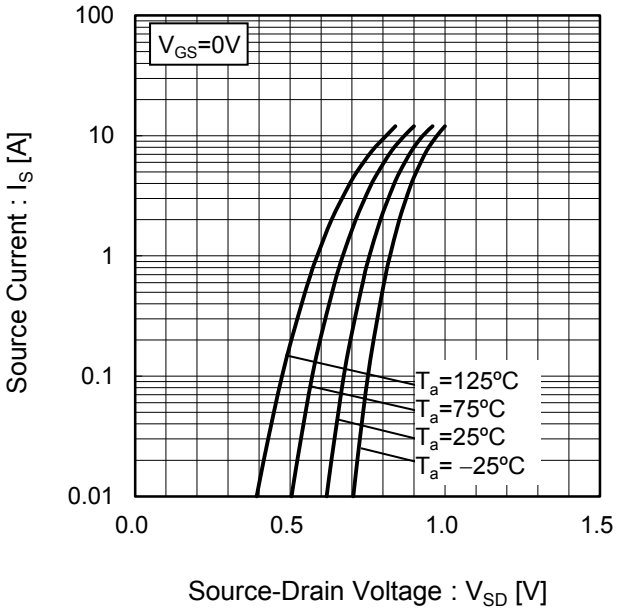
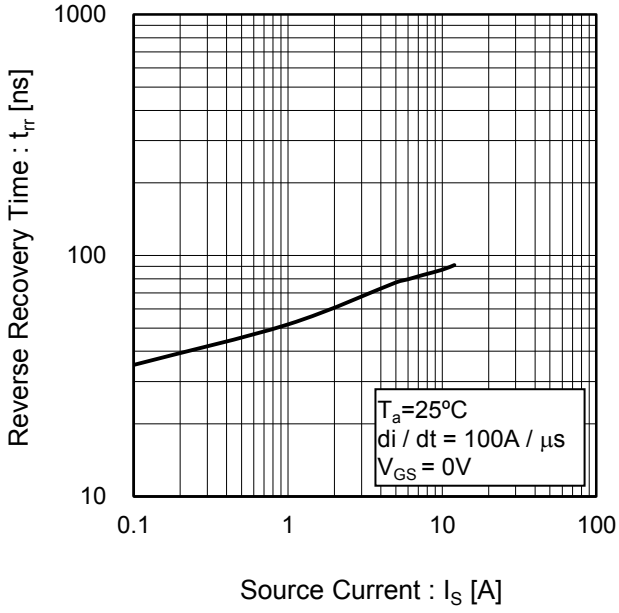


Fig21 Reverse Recovery Time vs.Source Current



●Measurement circuits

Fig.1-1 Switching Time Measurement Circuit

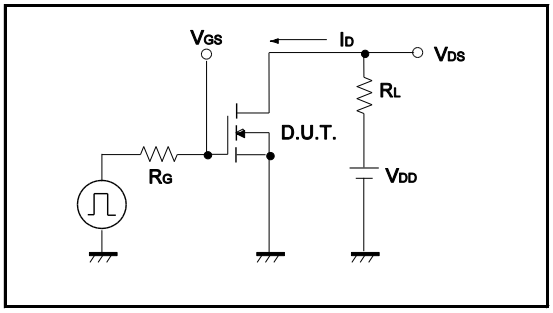


Fig.1-2 Switching Waveforms

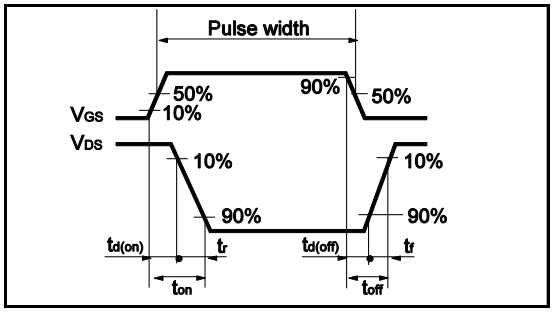


Fig.2-1 Gate Charge Measurement Circuit

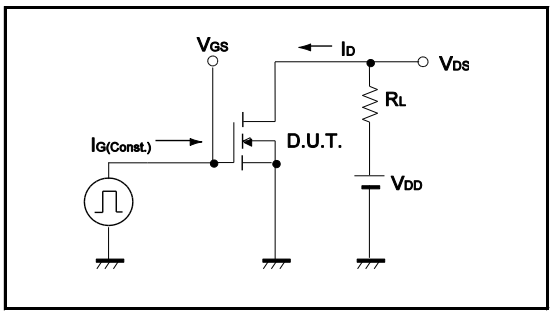


Fig.2-2 Gate Charge Waveform

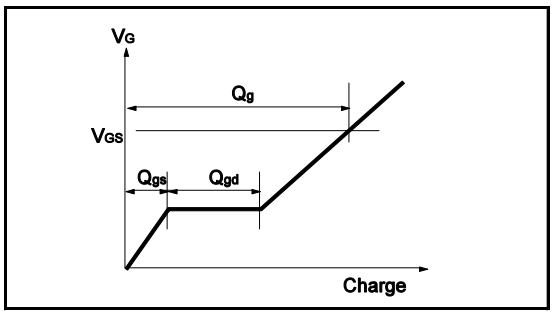


Fig.3-1 Avalanche Measurement Circuit

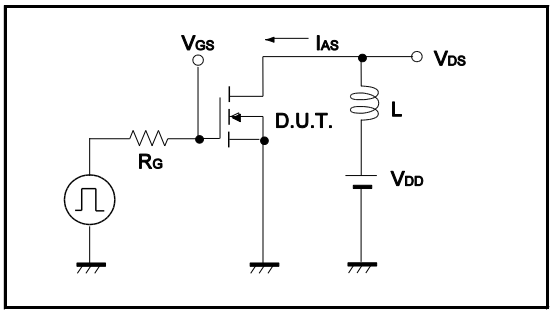
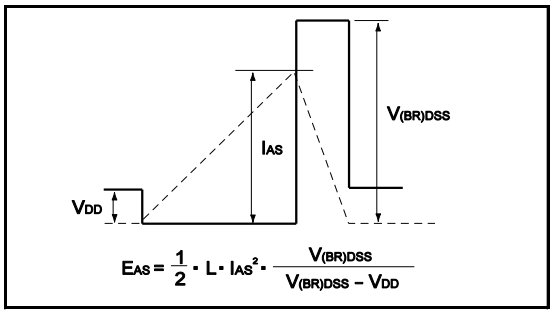


Fig.3-2 Avalanche Waveform



●**Dimensions** (Unit : mm)

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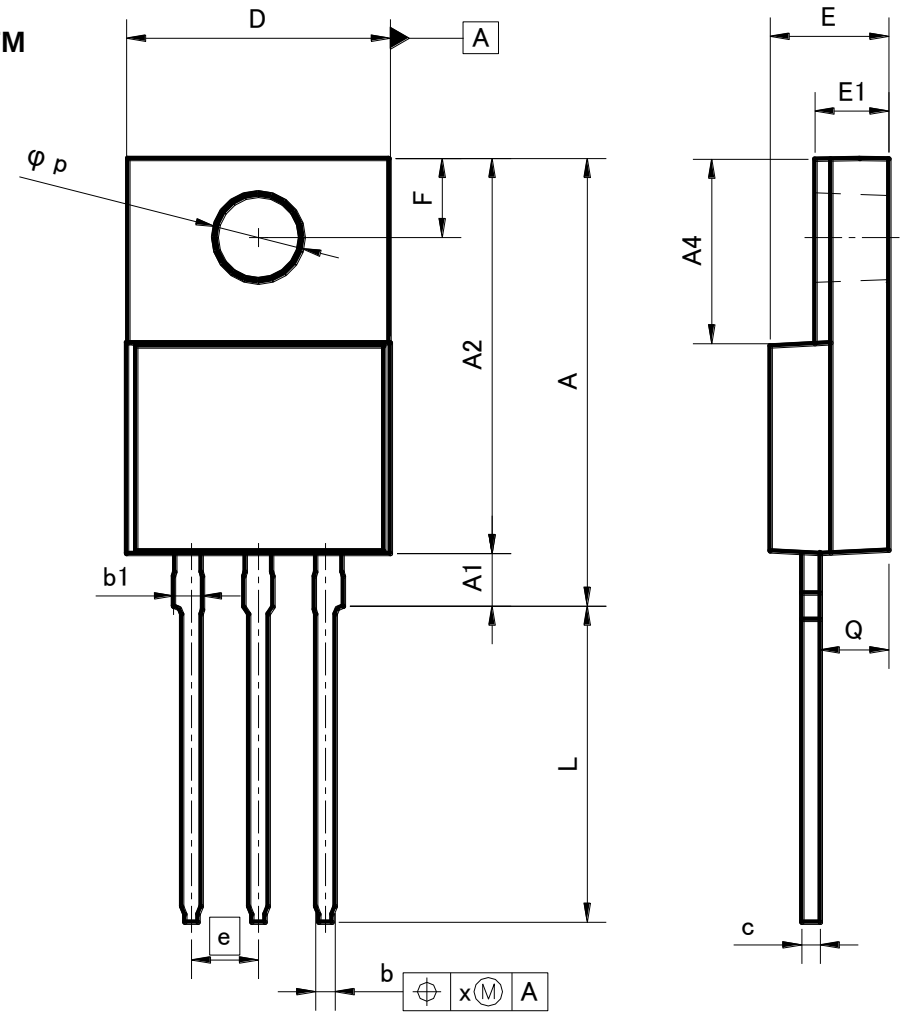

DIM	MILIMETERS		INCHES	
	MIN	MAX	MIN	MAX
A	16.60	17.60	0.654	0.693
A1	1.80	2.20	0.071	0.087
A2	14.80	15.40	0.583	0.606
A4	6.80	7.20	0.268	0.283
b	0.70	0.85	0.028	0.033
b1	1.10	1.50	0.043	0.059
c	0.70	0.85	0.028	0.033
D	9.90	10.30	0.39	0.406
E	4.40	4.80	0.173	0.189
e	2.54		0.10	
E1	2.70	3.00	0.106	0.118
F	2.80	3.20	0.11	0.126
L	11.50	12.50	0.453	0.492
p	3.00	3.40	0.118	0.134
Q	2.10	3.10	0.083	0.122
x	−	0.381	−	0.015

Dimension in mm/inches

Notes

1) The information contained herein is subject to change without notice.

2) Before you use our Products, please contact our sales representative and verify the latest specifications :

3) Although ROHM is continuously working to improve product reliability and quality, semiconductors can break down and malfunction due to various factors.
Therefore, in order to prevent personal injury or fire arising from failure, please take safety measures such as complying with the derating characteristics, implementing redundant and fire prevention designs, and utilizing backups and fail-safe procedures. ROHM shall have no responsibility for any damages arising out of the use of our Poducts beyond the rating specified by ROHM.

4) Examples of application circuits, circuit constants and any other information contained herein are provided only to illustrate the standard usage and operations of the Products. The peripheral conditions must be taken into account when designing circuits for mass production.

5) The technical information specified herein is intended only to show the typical functions of and examples of application circuits for the Products. ROHM does not grant you, explicitly or implicitly, any license to use or exercise intellectual property or other rights held by ROHM or any other parties. ROHM shall have no responsibility whatsoever for any dispute arising out of the use of such technical information.

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7) The Products specified in this document are not designed to be radiation tolerant.

8) For use of our Products in applications requiring a high degree of reliability (as exemplified below), please contact and consult with a ROHM representative : transportation equipment (i.e. cars, ships, trains), primary communication equipment, traffic lights, fire/crime prevention, safety equipment, medical systems, servers, solar cells, and power transmission systems.

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